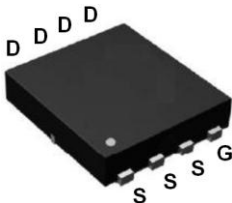

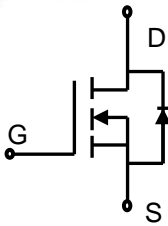



Lonten N-channel 60V, 80A, 6.2mΩ Power MOSFET

<p>Description These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ 60V,80A,$R_{DS(on),max}=6.2m\Omega@V_{GS}=10V$ ◆ Improved dv/dt capability ◆ Fast switching ◆ 100% EAS Guaranteed ◆ Green device available <p>Applications</p> <ul style="list-style-type: none"> ◆ Motor Drives ◆ UPS ◆ DC-DC Converter 	<p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="padding: 2px;">V_{DSS}</td> <td style="padding: 2px; text-align: right;">60V</td> </tr> <tr> <td style="padding: 2px;">$R_{DS(on),max}@V_{GS}=10V$</td> <td style="padding: 2px; text-align: right;">6.2mΩ</td> </tr> <tr> <td style="padding: 2px;">I_D</td> <td style="padding: 2px; text-align: right;">80A</td> </tr> </table> <p>Pin Configuration</p> <div style="text-align: center;">   <p style="margin-top: 10px;">PPAK5×6</p>  </div> <p style="text-align: center; margin-top: 20px;">N-Channel MOSFET </p>	V_{DSS}	60V	$R_{DS(on),max}@V_{GS}=10V$	6.2mΩ	I_D	80A
V_{DSS}	60V						
$R_{DS(on),max}@V_{GS}=10V$	6.2mΩ						
I_D	80A						

Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Continuous drain current ($T_C = 25^\circ C$) ¹⁾	I_D	80	A
Continuous drain current ($T_C = 100^\circ C$) ¹⁾		58	A
Pulsed drain current ²⁾	I_{DM}	280	A
Gate-Source voltage	V_{GSS}	± 20	V
Avalanche energy ³⁾	E_{AS}	259	mJ
Power Dissipation ($T_C = 25^\circ C$)	P_D	96	W
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.3	$^\circ C/W$

Package Marking and Ordering Information

Device	Device Package	Marking
LNN06R062	PPAK5×6	LNN06R062

Electrical Characteristics
 $T_J = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=250\mu\text{A}$	60	---	---	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	---	3.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_J = 25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_J = 125^\circ\text{C}$	---	---	5	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$	---	4.9	6.2	m Ω
		$V_{GS}=4.5\text{ V}, I_D=10\text{ A}$	---	7.2	10	m Ω
Forward transconductance	g_{fs}	$V_{DS}=5\text{ V}, I_D=50\text{ A}$	---	56	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS}=30\text{ V}, V_{GS}=0\text{ V},$ $F=1\text{ MHz}$	---	6080	---	pF
Output capacitance	C_{oss}		---	393	---	
Reverse transfer capacitance	C_{rss}		---	192	---	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V}, I_D=10\text{ A}$	---	15	---	ns
Rise time	t_r		---	13	---	
Turn-off delay time	$t_{d(off)}$		---	50	---	
Fall time	t_f		---	36	---	
Gate resistance	R_g	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}, F=1\text{ MHz}$	---	2.44	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DS}=30\text{ V}, I_D=40\text{ A},$ $V_{GS}=10\text{ V}$	---	26.6	---	nC
Gate to drain charge	Q_{gd}		---	37.9	---	
Gate charge total	Q_g		---	130	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	80	A
Pulsed Source Current ⁴⁾	I_{SM}		---	---	280	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{ V}, I_S=40\text{ A}, T_J=25^\circ\text{C}$	---	0.95	1.4	V
Reverse Recovery Time	t_{rr}	$I_S=40\text{ A}, di/dt=100\text{ A}/\mu\text{s},$ $T_J=25^\circ\text{C}$	---	50	---	ns
Reverse Recovery Charge	Q_{rr}		---	80	---	nC

Notes:

- 1: The maximum junction current rating is package limited.
- 2: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3: $V_{DD}=50\text{ V}, V_{GS}=10\text{ V}, L=0.1\text{ mH}, I_{AS}=72\text{ A}, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
- 4: Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

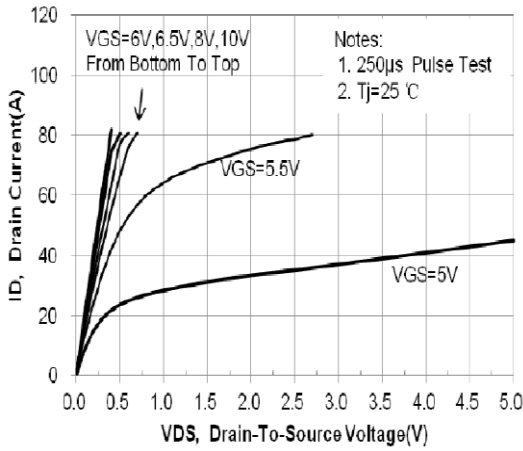


Figure 2. Transfer Characteristics

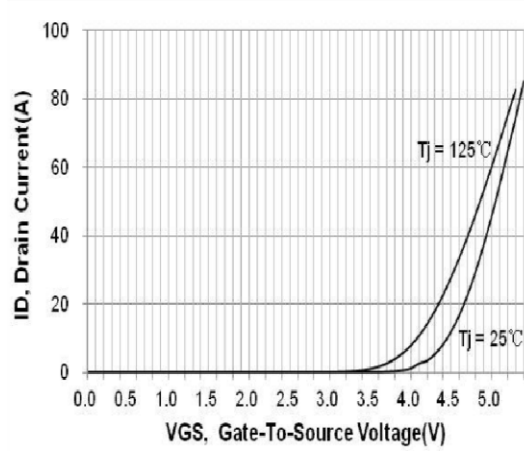


Figure 3. Capacitance Characteristics

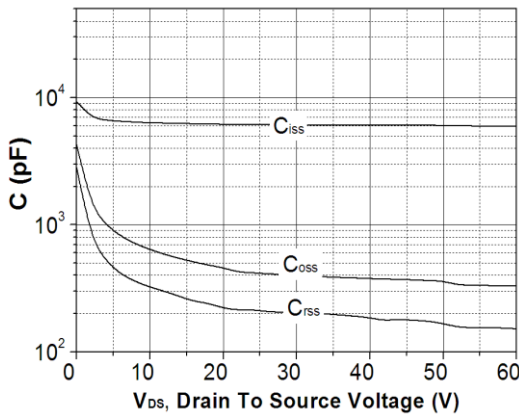


Figure 4. Gate Charge Waveform

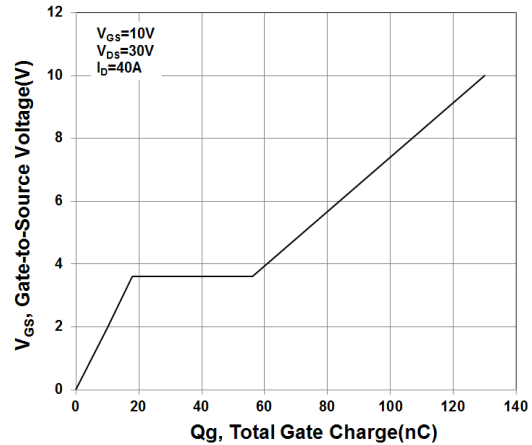


Figure 5. Body-Diode Characteristics

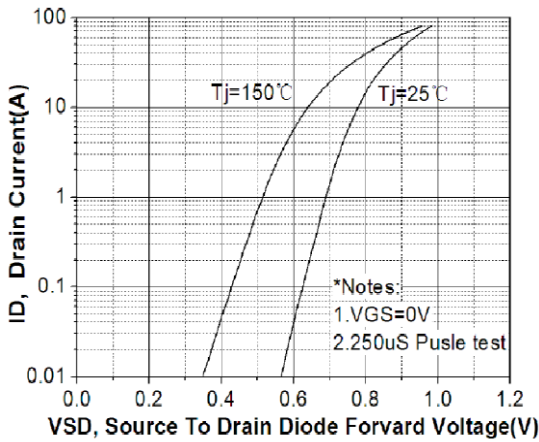
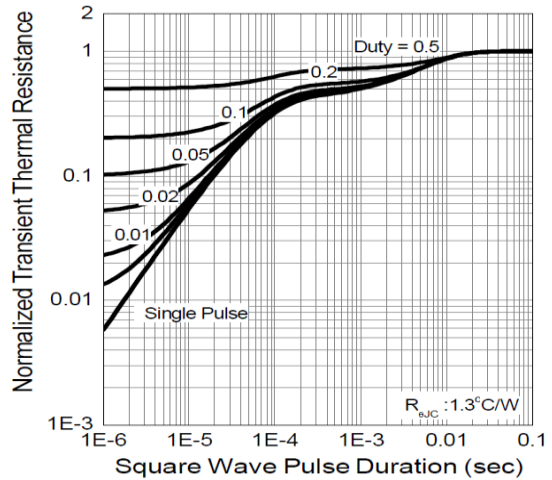


Figure 6. Thermal Transient Impedance



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

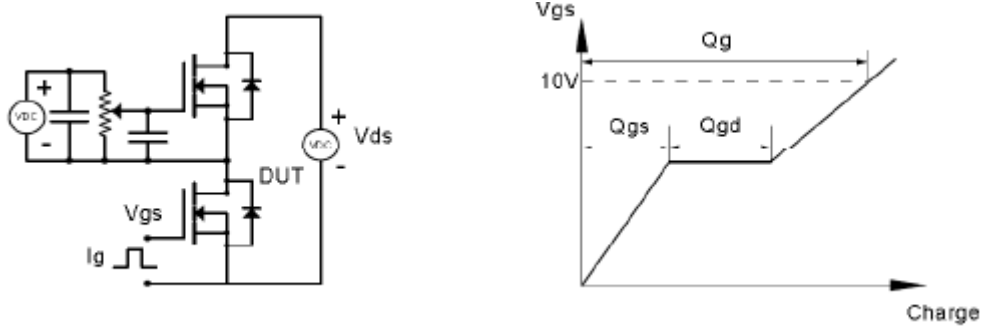


Figure 9. Resistive Switching Test Circuit & Waveforms

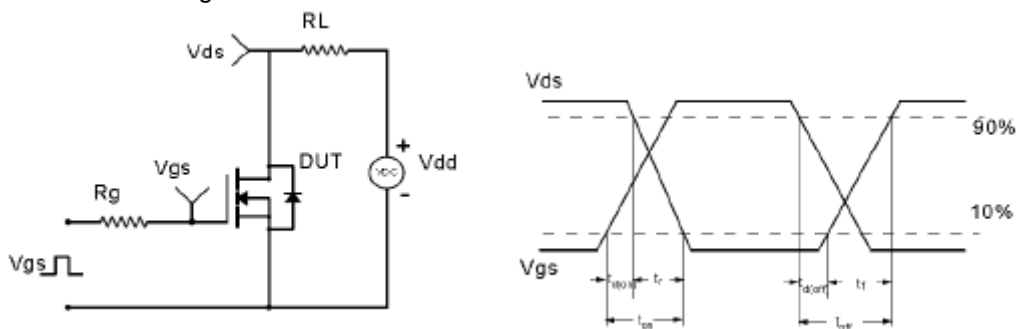


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

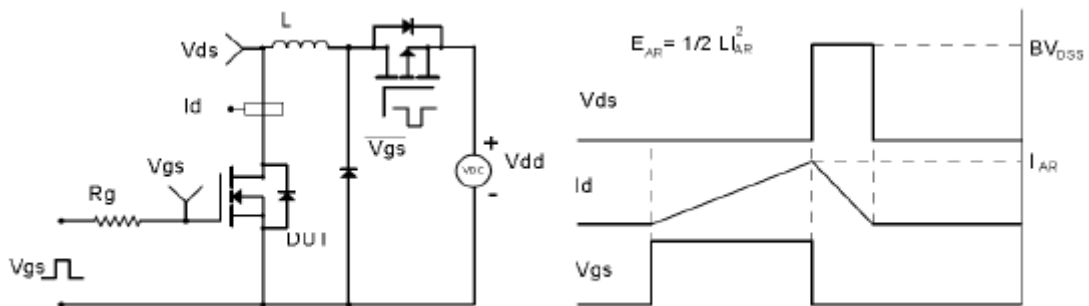
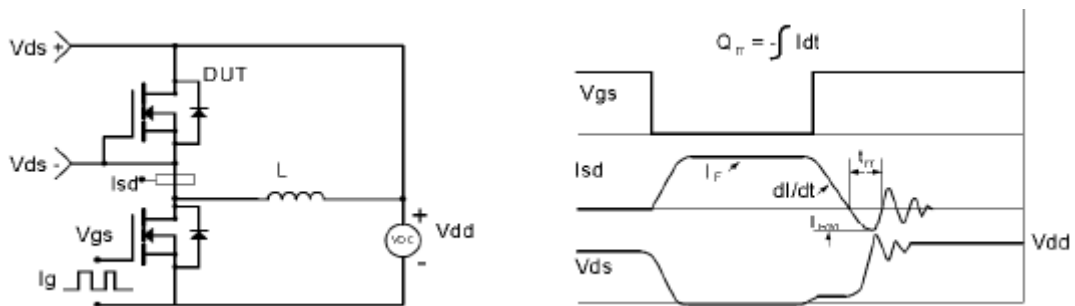
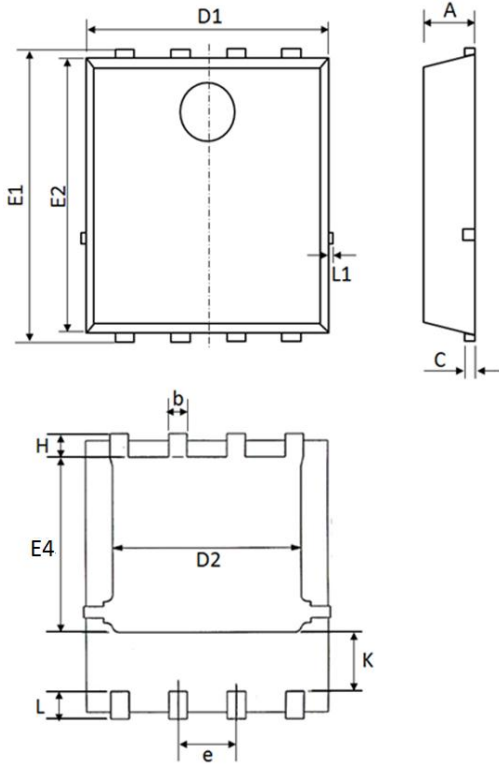


Figure 11. Diode Recovery Circuit & Waveform

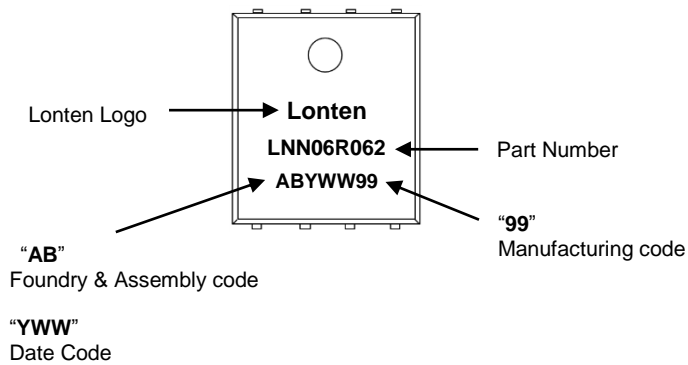


Mechanical Dimensions for PPAK5×6



COMMON DIMENSIONS						
SYMBOL	MILLIMETERS			INCHS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1	1.1	1.2	0.039	0.043	0.047
b	0.3	0.4	0.5	0.012	0.016	0.020
C	0.154	0.254	0.354	0.006	0.010	0.014
D1	5	5.2	5.4	0.197	0.205	0.213
D2	3.8	4.1	4.25	0.150	0.161	0.167
E1	5.95	6.15	6.35	0.234	0.242	0.250
E2	5.66	5.86	6.06	0.223	0.231	0.239
E4	3.52	3.72	3.92	0.139	0.146	0.154
e	1.27 BSC			0.050 BSC		
H	0.4	0.5	0.6	0.016	0.020	0.024
L	0.5	0.6	0.7	0.020	0.024	0.028
L1	-	-	0.12	-	-	0.005
K	1.14	1.29	1.44	0.045	0.051	0.057

PPAK5×6 Part Marking Information



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